

Amendments to the Claims

This listing of claims replaces all prior versions of claims in the application.

1. (Currently Amended) A semiconductor device including a gate having a gate insulation film and a gate electrode, a source, and a drain, said semiconductor device comprising:
a sidewall film ~~covering~~ contacting a side surface of said gate; and
a low permittivity region locally provided at a lower portion of the side surface of said gate with the low permittivity region being covered by said sidewall film,
wherein said gate insulation film and a lower end of said gate electrode have a same width as each other;
wherein said low permittivity region is made of a lower permittivity material as compared to said sidewall film;
wherein said sidewall film includes
a first film directly formed at an upper portion of said side surface of said gate, and
a second film formed on said first film to directly contact said low permittivity region directly formed at the lower portion of the side surface of said gate;
wherein said gate electrode has a nearly rectangular shaped section.

Claims 2-5 (Cancelled)

6. (Original) The semiconductor device according to claim 1, wherein a part of a side wall lower portion of said gate is removed to have said low permittivity region formed into a notched shape.

7. (Original) The semiconductor device according to claim 6, wherein said low permittivity region is made of a lower permittivity material as compared to said sidewall film.

8. (Original) The semiconductor device according to claim 6, wherein said low permittivity region is a cavity.

9-12 (Canceled)

13. (New) A semiconductor device including a gate having a gate insulation film and a gate electrode, a source, and a drain, said semiconductor device comprising:

a sidewall film contacting a side surface of said gate; and

a low permittivity region locally provided at a lower portion of the side surface of said gate with the low permittivity region being covered by said sidewall film,

wherein said gate insulation film and a lower end of said gate electrode have a same width as each other;

wherein said low permittivity region is a cavity;

wherein said sidewall film includes

a first film directly formed only at an upper portion of said side surface of said gate, and

a third film covering said first film, to form the cavity only at a lower portion of said side surface, said cavity formed to directly contact both sides of a lower portion of said gate; and

wherein said gate electrode has a nearly rectangular shaped section.

14. (New) A semiconductor device including a gate having a gate insulation film and a gate electrode, a source, and a drain, said semiconductor device comprising:

a sidewall film contacting a side surface of said gate; and

a low permittivity region locally provided at a lower portion of the side surface of said gate with the low permittivity region being covered by said sidewall film,

wherein said gate insulation film and a lower end of said gate electrode have a same width as each other;
wherein a part of a side wall lower portion of said gate is removed to have said low permittivity region formed into a notched shape.

15. (New) The semiconductor device according to claim 14, wherein said low permittivity region is made of a lower permittivity material as compared to said sidewall film.

16. (New) The semiconductor device according to claim 14, wherein said low permittivity region is a cavity.